

March 2010

BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

General Description

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

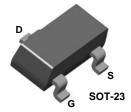
Features

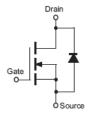
- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.

BS170

MMBF170







Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
V _{DSS}	Drain-Source Voltage	6	V	
V _{DGR}	Drain-Gate Voltage ($R_{GS} \le 1M\Omega$)	6	V	
V _{GSS}	Gate-Source Voltage	±	V	
I _D	Drain Current - Continuous	500	500	mA
	- Pulsed	1200	800	111/
T _J , T _{STG}	Operating and Storage Temperature Range	- 55 t	°C	
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	30	°C	

Thermal Characteristics $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
P _D	Maximum Power Dissipation Derate above 25°C	<mark>830</mark> 6.6	300 2.4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	150	417	°C/W

$\textbf{Electrical Characteristics} \quad \textbf{T}_{A}\text{=}25^{\circ}\text{C unless otherwise noted}$

Symbol	Parameter	Conditions	Туре	Min.	Тур.	Max.	Units
OFF CHA	RACTERISTICS	1	1		I		ı
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 100\mu A$	All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	All			0.5	μΑ
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 15V$, $V_{DS} = 0V$	All			10	nA
ON CHAR	RACTERISTICS (Notes 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1mA$	All	8.0	2.1	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 200mA$	All		1.2	5	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 200 \text{mA}$	BS170		320		mS
		$V_{DS} \ge 2 V_{DS(on)},$ $I_D = 200 \text{mA}$	MMBF170		320		
Dynamic	Characteristics					•	
C _{iss}	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	All		24	40	pF
C _{oss}	Output Capacitance	f = 1.0MHz	All		17	30	pF
C _{rss}	Reverse Transfer Capacitance		All		7	10	pF
Switching	Characteristics (Notes 1)						
t _{on}	Turn-On Time	$V_{DD} = 25V, I_{D} = 200mA, V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_{D} = 500mA, V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	
t _{off}	Turn-Off Time	$V_{DD} = 25V, I_{D} = 200 \text{mA}, \ V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_{D} = 500 \text{mA},$ $V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	

Note:

Ordering Information

Part Number	Package	Package Type	Lead Frame	Pin array
BS170	TO-92	BULK	STRAIGHT	DGS
BS170_D26Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D27Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D74Z	TO-92	AMMO	FORMING	DGS
BS170_D75Z	TO-92	AMMO	FORMING	DGS
MMBF170	SOT-23	Tape and Reel		

^{1.} Pulse Test: Pulse Width $\leq~300\mu s$, Duty Cycle $\leq~2.0\%$.

Typical Electrical Characteristics

BS170 / MMBF170

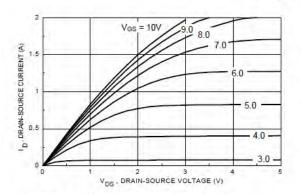


Figure 1. On-Region Characteristics.

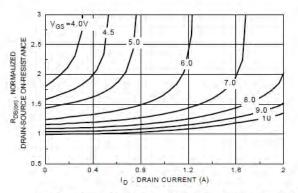


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

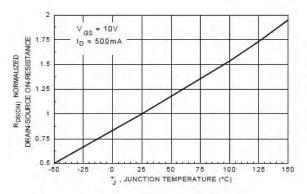


Figure 3. On-Resistance Variation with Temperature.

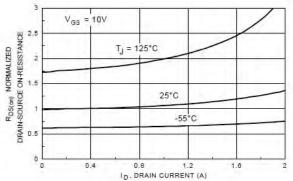


Figure 4. On-Resistance Variation with Drain Current and Temperature.

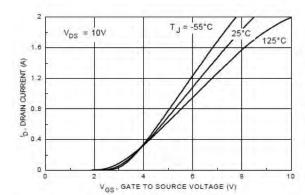


Figure 5. Transfer Characteristics.

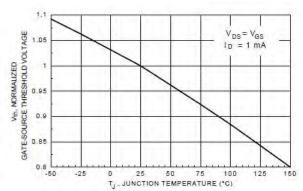


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

BS170 / MMBF170

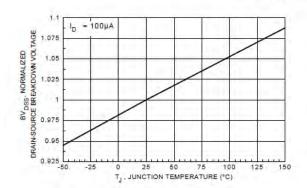


Figure 7. Breakdown Voltage Variation with Temperature.

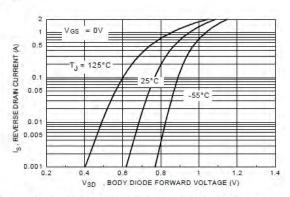


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

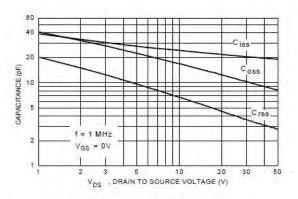


Figure 9. Capacitance Characteristics.

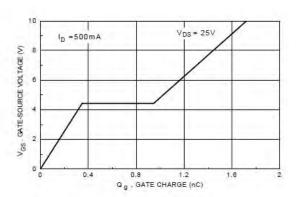


Figure 10. Gate Charge Characteristics.

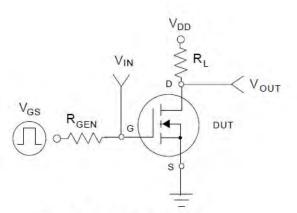


Figure 11. Switching Test Circuit.

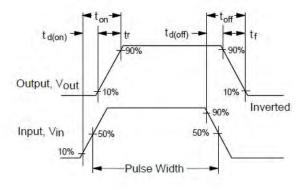
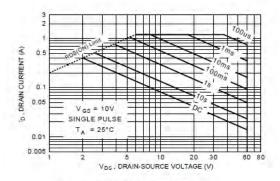


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)



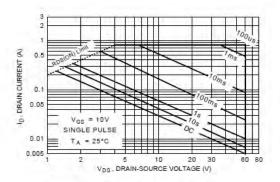


Figure 13. BS170 Maximum Safe Operating Area.

Figure 14. MMBF170 Maximum Safe Operating Area.

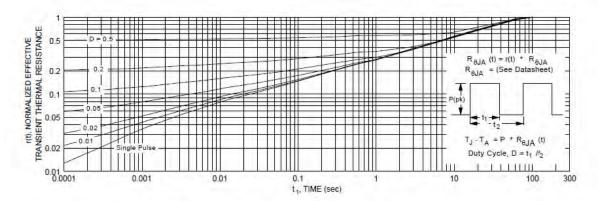


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

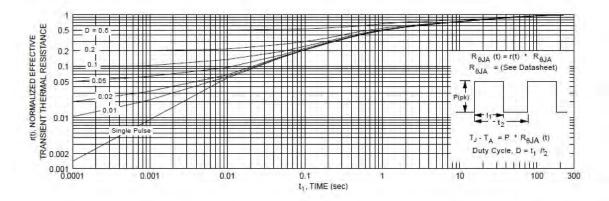
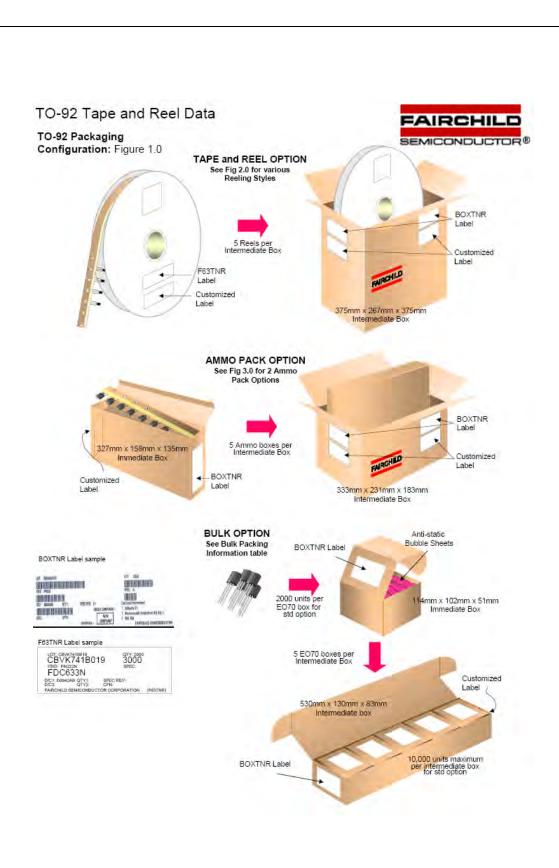


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.



TO-92 Tape and Reel Data, continued



TO-92 Packing Information: Figure 2.0

TO-92 TNR/AMMO PACKING INFORMATION TABLE

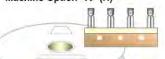
Packing	Style	Quantity	EOL code
Reel	Α	2,000	D26Z
	В	2,000	D11Z
	C	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
	H.	2,000	D69Z
Anima	M	2,000	D74Z
-	P P	2,000	D75Z

Unit weight = 0.22 gm
Reel weight with components = 1,04 kg
Amma weight with components = 1,02 kg
Max quantity per infermediate box = 10,000 units

TO-92 BULK PACKING INFORMATION TABLE

FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OULTINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	1
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0K / BOX	19
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	19
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	19
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	19
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	-

TO-92 Tape and Reel Data, continued TO-92 Reeling Style Configuration: Figure 3.0 Machine Option "A" (H)



Style "A", D26Z



Style "B", D11Z



Style "C", D28Z

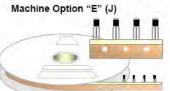


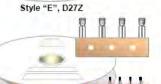
Style "D", D10Z

TO-92 Radial Ammo Packaging Configuration: Figure 4.0









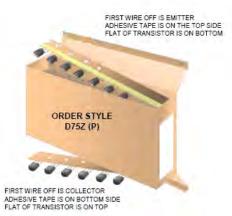
Style "F", D81Z

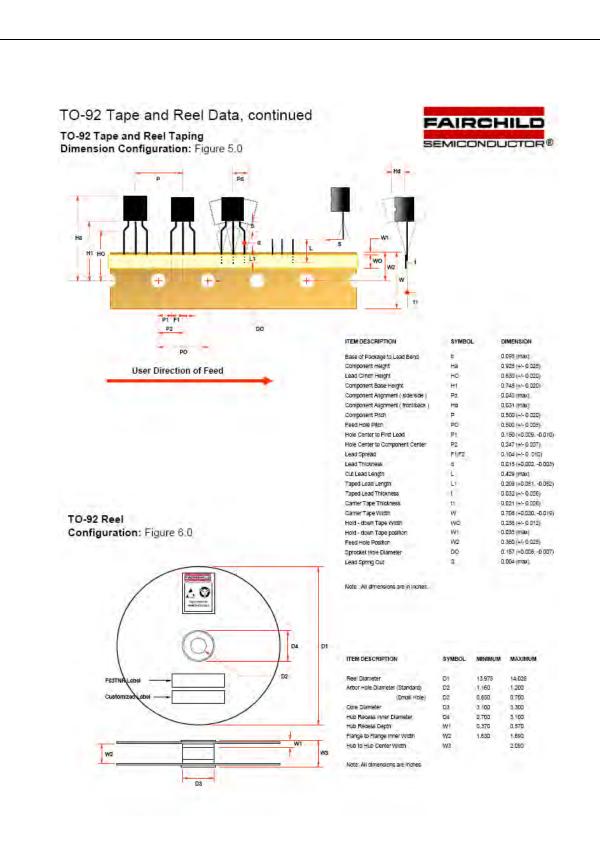


Style "G", D29Z



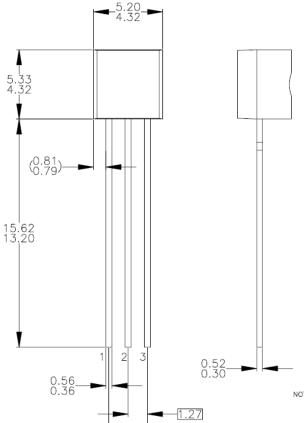
Style "H", D89Z

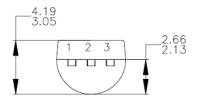




Mechanical Dimensions (TO-92)

TO-92





2.54

NOTES: UNLESS OTHERWISE SPECIFIED

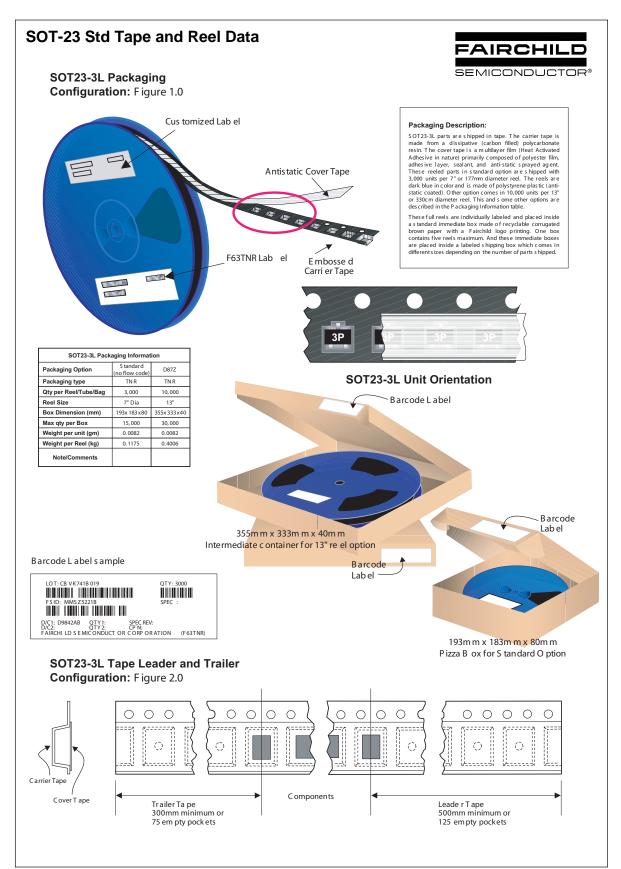
- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS. ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-1994. TO-92 (92,94,96,97,98) PIN CONFIGURATION:

1 E S S E S S B D G C G D C G	14		98			97			96					92		z
1 2 3 3 2 3 3 8 8 8 8 8 8 8 8 8	M	F	Р	М	F	Р	М	F	Ρ	М	F	Р	М	F	Р	₫.
	D	G	С	D	G	С	G	D	В	S	S	Ε	S	S	Ε	1
2 B D G C G D E S S B D G E S	S	S	Ε	G	D	В	S	S	Е	D	G	С	G	D	В	2
3 C G D B D G C G D E S S B D	G	D	В	S	S	Ε	D	G	С	G	D	В	D	G	С	3

LEGEND: P - BIPOLAR F - JFET M - DMOS E - EMITTER B - BASE C - COLLECTOR D - DRAIN S - SOURCE G - GATE

- FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "O" AND SOURCE "S" ARE INTERCHANGEAGLE AT JFET "F" OPTION. DRAWING FILENAME: MKT-ZAO3DREV3. E)

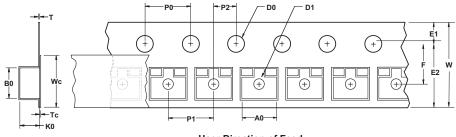
Dimensions in Millimeters





SOT23-3L Embossed Carrier Tape

Configuration: Figure 3.0



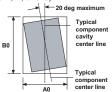
User D	irection of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



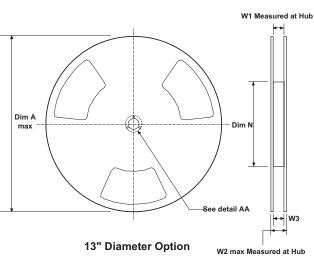
Sketch B (Top View)
Component Rotation

Dim A Max



Sketch C (Top View)
Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0



Dim D

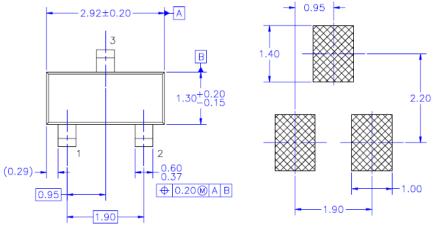
Dim C

7" Diameter Option

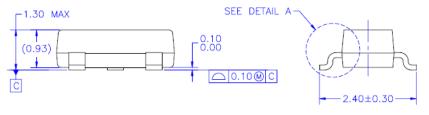
DETAIL AA Dimensions are in inches and millimeters Tape Size Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W3 (LSL-USL) 512 +0.020/-0.008 13 +0.5/-0.2 0.331 +0.059/-0.000 8.4 +1.5/0 7" Dia 8mm 0.311 - 0.429 7.9 - 10. 9 13" Dia

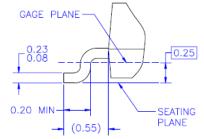
Mechanical Dimensions (SOT-23)

SOT-23



LAND PATTERN RECOMMENDATION





DETAIL A

NOTES: UNLESS OTHERWISE SPECIFIED

- REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
 ALL DIMENSIONS ARE IN MILLIMETERS.
 DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
 DRAWING FILE NAME: MAO3DREV9

Dimensions in Millimeters





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Gmax™

GTO™

IntelliMAX™

MicroPak™

MicroPak2™

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CTL™

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EcoSPARK[®]
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SuperSOT™-8
SupreMOS™
SyncFET™
Sync-Lock™

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Franchise
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Definition of Terms

Definition of Terms								
Product Status	Definition							
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First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.							
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